

PMP41017_GaNBoard REV E1 Bill of Materials

Designator	Quantity	Value	PartNumber	Manufacturer	Description	PackageReference
C57, C62	2	10uF	C1206C106K3RACTU	Kemet	CAP, CERM, 10 uF, 25 V, +/- 10%, X7R, 1206_190	1206_190
C58, C63	2	0.22uF	CL05B224KO5NNNC	Samsung Electro-Mechanics	CAP, CERM, 0.22 uF, 16 V, +/- 10%, X7R, 0402	402
C59, C64	2	2.2uF	GRM219R61E225KA12D	MuRata	CAP, CERM, 2.2 uF, 25 V, +/- 10%, X5R, 0805	805
C61, C170	2	100pF	8.85012E+11	Wurth Elektronik	CAP, CERM, 100 pF, 50 V, +/- 10%, X7R, 0402	402
C65, C66, C67, C68	4	0.022uF	C1206C223KDRACTU	Kemet	CAP, CERM, 0.022 uF, 1000 V, +/- 10%, X7R, AEC-Q200 Grade 1, 1206	1206
D1	1	1000V	US1M-13-F	Diodes Inc.	Diode, Ultrafast, 1000 V, 1 A, SMA	SMA
D2	1	16V	BZT52C16-7-F	Diodes Inc.	Diode, Zener, 16 V, 500 mW, AEC-Q101, SOD-123	SOD-123
L1, L4	2		SDEM20161T-4R7MS	Cyntec	4.7uH Unshielded Inductor 1.1A 426mOhm Max 0806 (2016 Metric)	SMD2
R24	1	2	MCT06030C2008FP500	Vishay/Beyschlag	RES, 2.00, 1%, 0.125 W, 0603	603
R25, R28	2	0	MCR01MZPJ000	Rohm	RES, 0, 5%, 0.063 W, 0402	402
R27, R110	2	300	CRCW0402300RJNED	Vishay-Dale	RES, 300, 5%, 0.063 W, AEC-Q200 Grade 0, 0402	402
U7, U8	2	50mR	LMG3422R050RQZR	Texas Instruments	600-V 50-mΩ Integrated GaN Power Stage with Smart Driver	VQFN54